FAIRCHILD
SEMICONDUCTOR®

QFET™

FQA9N90C

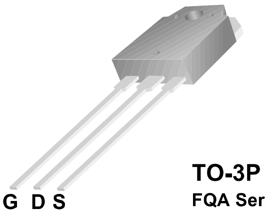
900V N-Channel MOSFET

General Description

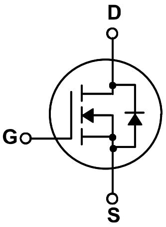
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies.

Features

- 9A, 900V, $R_{DS(on)}$ = 1.4Ω @V_{GS} = 10 V
- Low gate charge (typical 45 nC)
- Low Crss (typical 14 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-3P
FQA Series



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FQA9N90C	Units
V_{DSS}	Drain-Source Voltage		900	V
I_D	Drain Current - Continuous (T_C = 25°C)		9.0	A
	- Continuous (T_C = 100°C)		5.7	A
I_{DM}	Drain Current - Pulsed	(Note 1)	36.0	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	900	mJ
I_{AR}	Avalanche Current	(Note 1)	9.0	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	28	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.0	V/ns
P_D	Power Dissipation (T_C = 25°C)		280	W
	- Derate above 25°C		2.22	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.45	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W